

※ 考生請注意：本試題可使用計算機。請於答案卷(卡)作答，於本試題紙上作答者，不予計分。

1. Consider the Zener diode circuit shown in Figure 1. The Zener breakdown voltage is $V_Z=5.6V$ at $I_Z=0.1mA$, and the incremental Zener resistance is $r_z=10\Omega$. (a) Determine V_O with no load ($R_L=\infty$). (b) Find the change in the output voltage if V_{PS} change by $\pm 1V$. (c) Find V_O if $V_{PS}=10V$ and $R_L=2k\Omega$. (15%)

2. Determine the Boolean expression for V_O in terms of the four input voltages for the circuit in Figure 2. (15%)

3. Consider the voltage reference circuit in Figure 3. Using a Zener diode with a breakdown voltage of $5.6V$. Design the circuit to produce an output voltage of $10V$. Assume the input voltage is $12V$, the R_2 current and R_4 current are $1mA$ and $2mA$ respectively, and the Zener diode current $I_Z=1mA$. (20%)

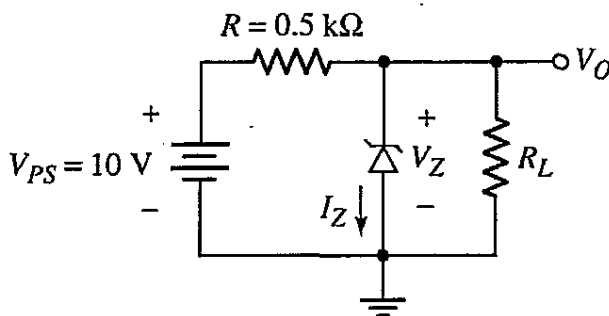


Fig.1

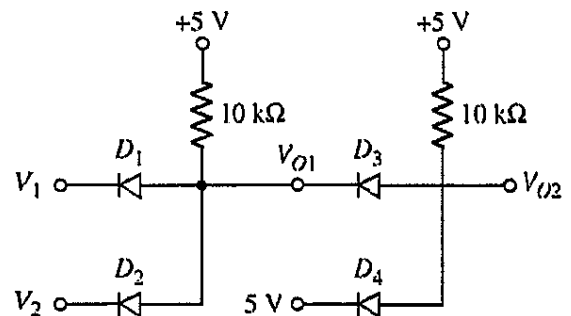


Fig. 2

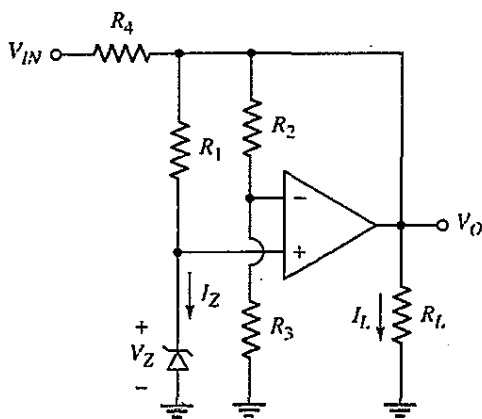


Fig.3

4、The transistor parameters in the circuit in Figure 4 are: $K_{n1}=0.1 \text{ mA/V}^2$, $K_{p2}=1.0 \text{ mA/V}^2$, $V_{TN1}=+2 \text{ V}$, $V_{TP2}=-2 \text{ V}$, and $\lambda_1=\lambda_2=0$. The circuit parameters are: $V_{DD}=10 \text{ V}$, $R_{S1}=4 \text{ k}\Omega$, and $R_{in}=200 \text{ k}\Omega$. (a) Design the circuit such that $I_{DQ1}=0.4 \text{ mA}$, $I_{DQ2}=2 \text{ mA}$, $V_{DSQ1}=4 \text{ V}$, and $V_{SDQ2}=5 \text{ V}$. (b) Calculate the small-signal voltage gain $A_v=v_o/v_i$. (c) Determine the maximum symmetrical swing in the output voltage. (20%)

5、Consider the current-to-voltage converter circuit shown in Figure 5. The input resistance R_{if} is assumed to be small, the output resistance is $R_o=0$, and the op-amp gain A_z is large. (20%)

(a) Write the closed-loop transfer function in the form

$$A_f = \frac{v_o}{i_s} = \frac{A_z}{(1 + \beta_g A_z)}$$

(b) What is the expression for β_g ?

(c) If $A_z = 5 \times 10^6 \Omega$ and $A_{zf} = 5 \times 10^4 \Omega$, what is the required β_g and R_F ?

(d) If A_z decrease by 10 percent, what is the percent change in A_{zf} ?

6、(a) Can two back-to-back connected p-n diodes be used as a transistor? Why? (5%)

(b) Describe the ideal OP-Amp characteristics? (5%)

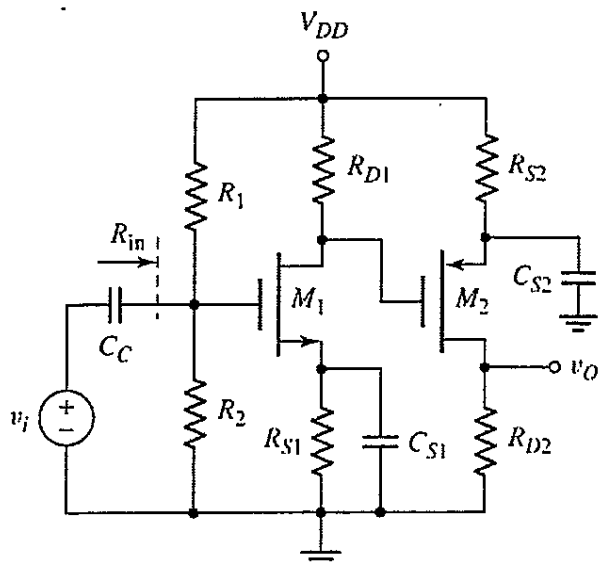


Fig.4

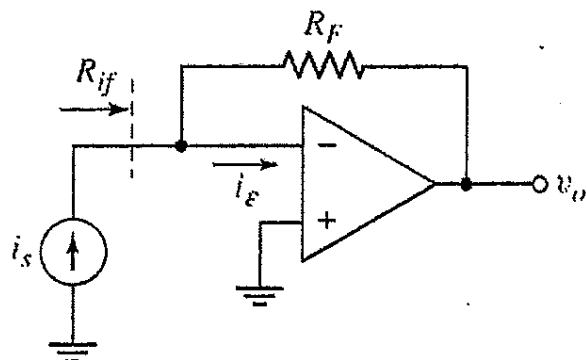


Fig.5